EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1253	117/90,94,104.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:02
L2	2	"thermal radiation absorption layer"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:02
L3	907	"TEOS oxide layer"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:03
L4	117412	"SiC"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:04
L5	1022	"highly doped silicon"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:04
L6	0	l4 near l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:05
L7	118894	l4 samr l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:05

L8	7	l4 same l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:05
L9	0	l1 and l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:06
L10	2	l3 and l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:06
L11	63	l4 and l5	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/05/13 18:06
S1	2	"20020028314"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:18
S2	9	"6447604"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/16 09:46
S3	27	"5771110"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/16 09:47
S4	11	"1143047"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/16 09:48
S5	19	"447047"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/16 09:47
S6	12	"1143047"	US-PGPUB; USPAT; USOCR; EPO; DERWENT	OR	OFF	2006/03/16 09:48
S7	94588	"silicon carbide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/03/16 09:55
S8	2	"thermal radiation absorption layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/03/16 09:55

S9	1	S7 and S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/03/16 09:56
S10	96	"radiation absorption layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/03/16 09:56
S11	3	S7 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2006/03/16 11:08
S12	1	"1184897"	EPO	OR	OFF	2006/03/16 11:09
S13	1	"1280190"	EPO	OR	OFF	2006/03/16 11:08
S14	7	"6214108"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 13:43
S15	2	"6824610"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 13:43
S16	226	117/94.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:19
S17	233	117/90.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:19
S18	16	"thermal absorption layer"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:19
S19	0	S16 and S18	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:19
S20	0	S17 and S18	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:28
S21	2842	"MOVPE"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 21:28
S22	0	S18 and S21	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:13
S23	372	117/104.ccls.	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:13
S24	0	S18 and S23	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:13

S25	8509	"absorption layer"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:13
S26	0	S23 and S25	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:14
S27	1627	"radiation layer"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:14
S28	0	S23 and S27	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:14
S29	25093	"TEOS"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:14
S30	663	"TEOS oxide layer"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:15
S31	0	S23 and S30	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:15
S32	0	S21 and S30	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:15
S33	84932	"siC"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:48
S34	84932	"SiC"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:48
S35	2842	"movpe"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:48
S36	741	S34 and S35	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:48
S37	67689	"backside"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:48
S38	39	S36 and S37	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:49
S39	105914	"polysilicon"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:49
S40	0	S38 and S39	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:49

S41	878176	"silicon"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:49
S42	21590	"doped silicon"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:49
S43	2	S38 and S42	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:58
S44	832	"AlGaInN"	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:58
S45	4	S34 near S44	US-PGPUB; USPAT; USOCR; DERWENT	OR	OFF	2006/03/17 22:58
S46	8788391	TW "447047" A	EPO; JPO	OR	OFF	2006/03/18 15:29
S47	1	"447047"	EPO; JPO	OR	OFF	2006/03/18 15:29
S48	5	"447047"	DERWENT	OR	OFF	2006/03/18 17:37
S49	1	"6927155"	DERWENT	OR	OFF	2006/03/18 17:39
S50	2	"6730939"	USPAT; DERWENT	OR	OFF	2006/03/18 17:38
S51	2	"6927155"	USPAT; DERWENT	OR	OFF	2006/03/18 17:39
S52	73863	"non-metallic"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 17:40
S53	84385	"backside"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 17:40
S54	872	S52 and S53	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 17:40
S55	101952	"silicon carbide"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2007/01/23 17:40

S56	65	S54 and S55	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:19
S57	109	"radiation absorption layer"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2007/01/23 17:41
S58	0	S56 and S57	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 17:41
S59	84385	"backside"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:19
S60	3388	"SiC Substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:19
S61	11	S59 near S60	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:40
S62	2237658	"substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:40
S63	18899	"underlayer"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:40
S64	1587	S62 near S63	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:40

S65	102070	"silicon carbide"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/01/23 18:41
S66	977	"highly doped silicon"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/18 18:39
S67	3908	"SiC substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/18 18:40
S68	2	"thermal radiation absorption layer"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/18 18:40
S69	0	S66 near S67	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/18 18:40
S70	0	S66 same S67	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/18 18:40
S71	5	S66 and S67	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:33
S72	1042	"highly doped polysilicon"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:41

S73	0	"under the substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:34
S74	4041	"substrate underlying"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:34
S75	0	S72 near S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:34
S76	1	S72 same S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:34
S77	8	S72 and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 11:34
S78	0	"highly doped polysilicone"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:02
S79	12	"1143047"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S80	2866	"rear side substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03

S81	268997	"rear side"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S82	2428803	"substrate"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S83	1904	"polysilicone"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S84	3276	S81 near S82	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S85	0	S83 near S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S86	0	S83 and S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S87	8	S83 same "116"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:03
S88	0	S83 same S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:04

S89	0	S83 and S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:08
S90	5	"highly doped silicone"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:08
S91	0	S83 and S90	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/12/20 12:08

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